



An Insight into the Electronic and Optical Characteristics of BaCu_2As_2 and $\alpha\text{-BaCu}_2\text{Sb}_2$ Compounds: An *Ab initio* Study

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Abstract

This report presents the first principle calculations of the electronic and optical characteristics of BaCu_2As_2 and $\alpha\text{-BaCu}_2\text{Sb}_2$ metallic compounds. The full potential linear augmented plane-wave (FPLAPW) technique is the basis for these computations. The exchange-correlation energy involves the contributions from the local density approximation (LDA), generalized gradient approximation (GGA) and Engel-Vosko generalized gradient approximation (EVGGA). As the EVGGA show better band splitting comparing to LDA and GGA therefore, we show the results of this approximation. The computed electronic band structures illustrate metallic nature of these compounds due to band's overlapping at the Fermi energy. The electronic density of states (total and partial DOS) of these compounds reveals that there exists strong hybridization between As/Sb-*p* and Cu-*d* states, with weak hybridization between Ba-*s* and Cu-*s* states and also between Cu-*d* and As-*d* states below the Fermi level (E_F). The As/Sb-*p* and Ba-*d* states contribute predominantly to the DOS at and above E_F . The origin of different features of optical properties are discussed based on band structure. The $\alpha\text{-BaCu}_2\text{Sb}_2$ compound demonstrates improved behavior in reflectivity as compared to that of BaCu_2As_2 compound. Due to this fact, the ability of reflecting solar light in $\alpha\text{-BaCu}_2\text{Sb}_2$ compound is more robust than that of BaCu_2As_2 .

Keywords: Electronic properties; Density of states; Local density approximation; Optical characteristics.

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1. Introduction

The modernization in superconductivity particularly in ternary pnictides and chalcogenides having tetragonal symmetry created prominence in the research area related to the discovery of superconductivity in the related iron-based compounds such as LaFePnO , LiFePn , and BaFe_2Pn_2 involving pnictogen (Pn) elements.^[1-5] The investigation on these iron-based superconductors was successively expanded into systems including other 3*d* transition metals. The experiments involving chemical doping in an anti-ferromagnetic BaFe_2As_2 led to superconductivity by electron incorporation using cobalt ($T_c = 22$ K)^[6] but not using chromium.^[7]

Fe chemical substitution with other 3*d* transition metals

consequences in a lot of different behaviors that consist of itinerant anti-ferromagnetism in BaCr_2As_2 ,^[8] anti-ferromagnetic insulation in BaMn_2As_2 ,^[9] correlated metallic effects in BaCo_2As_2 , and superconductivity in BaNi_2As_2 ($T_c = 0.6$ K).^[10] The theoretical study on BaCu_2As_2 compound illustrates its metallic and nonmagnetic behavior, with low-lying Cu-*d* states.^[11] The option of picking transition metals not only prompts the physical properties, but also influences the chemical bonding in these phases. Transition metals with additional electrons in the 3*d* orbitals acquire the configuration of homo-atomic Pn–Pn bonds that fix two nearby layers, and eventually, deform 2D structure into 3D network.^[12] The shaping of Pn₂ dimers is an imperative factor, which not only affects the crystal and electronic structures, magnetism, but also the existence of superconductivity in ternary pnictides with ThCr_2Si_2 -type structures.^[13-16] Previous studies by Pilchowski *et al.*^[17] demonstrate that $\text{Ba}_2\text{Cu}_3\text{P}_4$ is four times Cu deficit derivative of ThCr_2Si_2 -structure, and BaCu_2As_2 crystallizes with ThCr_2Si_2 structure. While BaCu_2Sb_2 ^[18] is based on ThCr_2Si_2 - and CaBe_2Ge_2 -type fragments with 1:2 ratio. In addition, some new diluted magnetic semiconductors involving hole- and spin-doped BaZn_2As_2 with 122-like phases were investigated by means of the first-principles

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calculations for basic structural, elastic, electronic properties and the peculiarities of the inter-atomic bondings.^[19] Though the physical properties of phosphide and arsenide compounds are not much recognized, β -BaCu₂Sb₂ appears to be a metallic compound with temperature-independent diamagnetic conduct.^[20] Saporov *et al.*^[21] has reported the synthesis, electrical resistivity, magnetization, single crystalline and powder X-ray diffraction investigations of BaCu₂As₂, BaCu₂Sb₂, and Ba₂Cu₃P₄ compounds. They also studied the thermal transport properties and Seebeck coefficients for BaCu₂As₂ resulting in small thermoelectric figure of merit. All of these compounds crystallize in different structures revealing close relation between them.^[21]

The present work was planned to study the electronic band structure, density of states, and also the optical properties of BaCu₂As₂ and α -BaCu₂Sb₂ using the full potential linear augmented plane wave (FP-LAPW) method within the framework of density functional theory (DFT). The computational method is discussed in the following Section 2. While section 3 reveals and explains the computed results and the short conclusion is presented in Section 4.

2. Computational method

The crystal structure of BaCu₂As₂ and α -BaCu₂Sb₂ has been illustrated in Fig. 1. These compounds possess tetragonal structure with space group D_{4h}^{17} I4/mmm and D_{4h}^7 P4/nmm for BaCu₂As₂ and α -BaCu₂Sb₂, respectively.^[22] The lattice constants for BaCu₂As₂ and α -BaCu₂Sb₂ compounds are $a = b = 4.4119(4)$ and $4.6536(3)$ Å and $c = 10.193(2)$ and $10.7946(13)$ Å, respectively.^[21] The present calculations are

performed using the full potential linearized augmented plane-wave (FP-LAPW) method based on the DFT^[23,24] as implemented in the Wien2k code.^[25] The exchange–correlation potentials are determined using the local density approximation (LDA), generalized gradient approximation (GGA) and Engel-Vosko generalized gradient approximation (EVGGA).^[26] The Kohn–Sham wave functions are expanded in terms of spherical harmonic functions inside the non-overlapping muffin-tin spheres (MT spheres) surrounding the atomic sites and in the Fourier series at the interstitial region. In the muffin-tin spheres of radius R_{MT} , l -expansion of the non-spherical potentials and charge density was carried out up to $l_{max} = 10$, while the magnitude of the largest vector in charge density Fourier expansion is $G_{max} = 12$ (Ryd)^{1/2}. The plane-wave cut-off $K_{max} = 8.0/R_{MT}$ is chosen for the expansion of wave functions at the interstitial site. The Ba, Cu, and As/Sb muffin-tin sphere radii are chosen as 2.0 Bohr. A mesh of 1000 special \mathbf{k} -points is made in the irreducible wedge of the first Brillouin zone (IBZ).

For analyzing the produced data and matching it with complex optical properties, Kramers-Kronig (KK) equations have been utilized. These equations facilitate to determine the real part of optical parameters by knowing their imaginary counterparts at all frequencies and vice versa. In the present case the imaginary part of the dielectric functions $\epsilon_2(\omega)$ has been computed using the following equation:^[27]

$$\epsilon_2^{ab}(\omega) = \sum_{nm} \int d\vec{k} f_{nm} \frac{\vartheta_{nm}^a(\vec{k}) \vartheta_{mn}^b(\vec{k})}{\omega_{mn}^2} \delta(\omega - \omega_{mn}(\vec{k})) \quad (1)$$

where ω determines the photon energy and $\omega_{mn}(k)$ gives the energy difference *i.e.*, $\omega_{mn}(k) = E_m(k) - E_n(k)$. The integration is performed over the first IBZ.

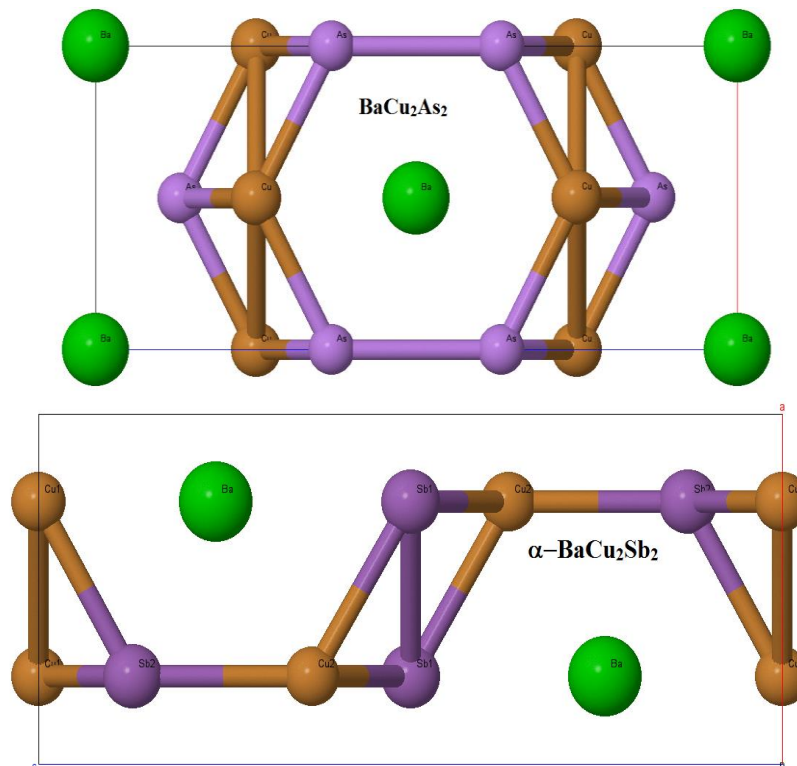


Fig. 1 Unit cell structures of BaCu₂As₂ and α -BaCu₂Sb₂ compounds.

3. Results and discussion

3.1 Electronic structure

The calculated self-consistent electronic band structures (BS) along the high symmetry directions for BaCu₂As₂ and α-BaCu₂Sb₂ compounds using EVGGA are demonstrated in Fig. 2. It is a well-known fact that being simple LDA and GGA approaches possess insufficient flexibility to accurately imitate both the exchange–correlation energies as well as their charge derivatives. Keeping in mind such shortcomings, Engel and Vosko developed a new functional form of GGA having capability for the reproduction of better exchange potentials at the expense of less agreement with the exchange energy. Such approach, named EVGGA, reveals relatively better band splitting and some other parameters that are mainly dependent on the exactness of exchange–correlation potentials. That is why, present results are being discussed only on the basis of EVGGA approach.^[28]

For the energy band calculations, Fermi level was set to be at 0.0 eV. Fig. 2 demonstrates the formation of impurity/localized states inside the band gap region close to Fermi level showing slight overlap of band states at the Fermi level in the case of BaCu₂As₂. However, due to the transfer of density of states from the valence to conduction band region, there exists strong overlapping of states at the Fermi level in the case of α-BaCu₂Sb₂ compound. It can be seen that several localized type energy states are distributed between the conduction as well as valence band and Fermi level in the band structure of α-BaCu₂Sb₂ compound. Such states may be created due to the contribution of spin-up and spin-down electrons making band structure relatively complex. Because of this, valence band maximum (VBM) extends towards Fermi level and to the conduction band minimum (CBM);

consequently, there is no band gap region. This is very much favorable for the enhancement of electrical conductivity of α-BaCu₂Sb₂ compound as compared to BaCu₂As₂ compound.^[29]

Figure 3(a) illustrates the calculated total density of state (TDOS) dispersion of BaCu₂As₂ and α-BaCu₂Sb₂ compounds using EVGGA approximation. It is noticed that the peaks of α-BaCu₂Sb₂ shifts towards higher energies with respect to BaCu₂As₂ as shown in Fig. 3(a). The total density of state of both compounds appears to be analogous except a few peaks depict different trend. Moreover, the magnitudes of TDOS peaks for BaCu₂As₂ compound are much smaller than those of α-BaCu₂Sb₂ compound. It is also obvious from these plots that both the valence and conduction bands overlap at the Fermi level illustrating zero band gap.

DOS plots provide a widespread representation of the elemental contributions to the electronic structure of various substances. DOS was calculated at Fermi level for these two (BaCu₂As₂ and α-BaCu₂Sb₂) compounds. The metallic character of both compounds is clearly visible from the nonzero DOS at the Fermi level as illustrated by Figs. 3(a-c). Fig. 3(b) clearly demonstrates strong contributions of Ba-*p* and As-*s* states with weak contributions of As-*s* and Cu-*s/p* states at about -14.0 eV and -11.0 eV, respectively. In addition, it is clear from Fig. 3(b) that the bands which exist in the energy range from -6.0 to 0.0 eV for BaCu₂As₂ compounds are due to Ba-*s* and Cu-*d* states along with weak involvement of the *s* state of Cu and As atoms, and also the *p* state of As and Cu atoms. Particularly a strong peak at about -3.0 eV is predominantly due to the Cu-*d*, and *s* states, As-*d* and Ba-*s* states. Similarly, Fig. 3(c) illustrates strong contributions at -14.0 eV and -9.0 eV caused by Ba-*p*, Sb-*s* states and Cu-*s/p* and Sb-*s* states with weak support from other states for the α-

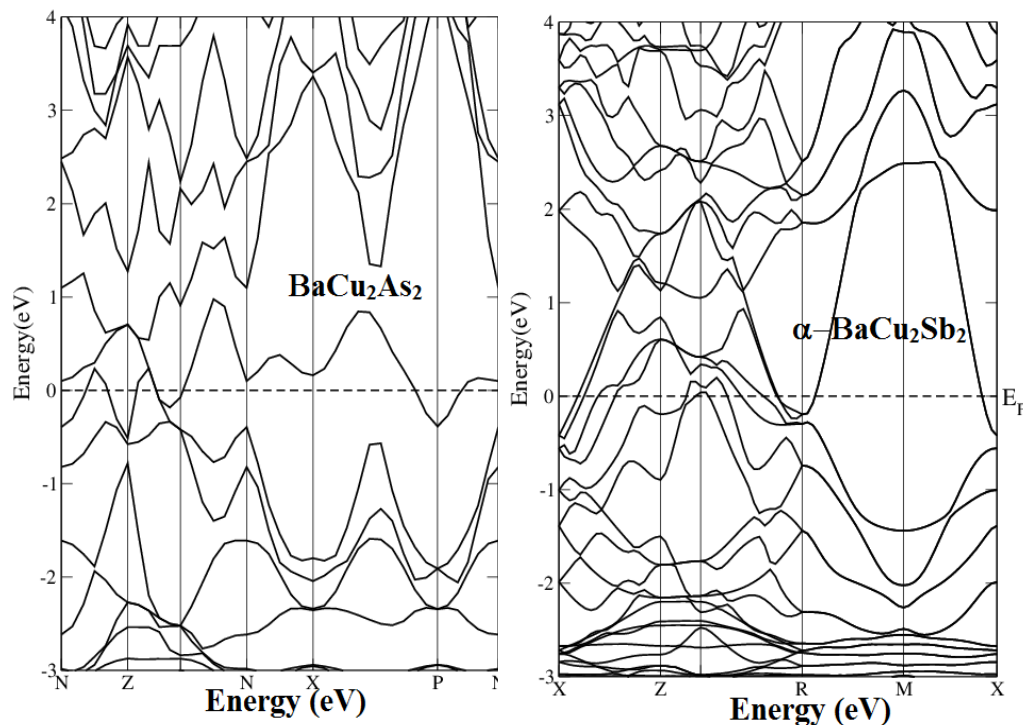


Fig. 2 Calculated band structures of BaCu₂As₂ and α-BaCu₂Sb₂ compounds.

BaCu₂Sb₂ compound. Whilst, in the energy range from -6.0 to 0.0 eV, dominant role is played by Cu-*d* states along with contributions from Sb-*p* and Cu-*s* states. A strong peak at about -3.0 eV is predominantly caused by Cu-*d*, and Sb-*p* states for the α-BaCu₂Sb₂ compound. In the vicinity of -3.0 eV band, strong hybridization exists between As/Sb-*p* and Cu-*d* states, with weak hybridization between Ba-*s* and Cu-*s* states and also between Cu-*d* and As-*d* states below the Fermi level. It is also noteworthy that the *p* states of As or Sb and Ba-*d* states mainly take part to add up in the density of states at the Fermi level. The present results are comparable with those of Wu *et al.*^[22] The collection of bands that are located above the Fermi level are mainly due to the Ba-*d*, Cu-*s/p* states and *p* states of As or Sb, whereas Cu-*s* and Cu-*p* states depict strong hybridization, these states also hybridize with Ba-*d* and As/Sb-*d* states which appears to account for the strong metallic character of these compounds. As most of the Cu-*d* states are observed at around 3.0 eV below the Fermi energy, the *d* orbital of Copper appears to be completely filled.^[22] Wu *et al.*^[22] suggested that the As-As interlayer bonding could not be responsible for Cu-3d¹⁰ configuration in BaCu₂As₂. Certainly, Cu-*d* states in α-BaCu₂Sb₂ are observed at almost the same energy as in BaCu₂As₂, in spite of the fact that Sb-Sb direct interlayer bonding are absent in the BaCu₂As₂ compound.^[22] In addition, Cu substitution appears as electron doping signifying that the local As-As and As-transition metal bonding are strongly affected.

Total DOS observed at Fermi level, $N(E_F)$, for BaCu₂As₂ and α-BaCu₂Sb₂ compounds are obtained as 1.37 and 3.16 states/eV-unit cell as obvious from Fig. 3(a). This figure illustrates that $N(E_F)$ is lower for BaCu₂As₂ as compared to that of α-BaCu₂Sb₂. The electronic specific heat coefficient (γ) has also been calculated, since it is a function of $N(E_F)$ as expressed by the relation^[27,30-37]

$$\gamma = \frac{1}{3} \pi^2 N(E_F) k_B^2 \quad (2)$$

where k_B represents the Boltzmann constant. The calculated values of γ are equal to 0.237 and 0.548 mJ/mol-K² in the case of BaCu₂As₂ and α-BaCu₂Sb₂, respectively. It is noticeable from Figs. 3(b) and 3(c) that key additions to the occupied region of DOS of valence band arises from the *d* states of Cu atoms and *p* states of Ba atoms, this behavior shows that the 'd' electrons of Cu atom transfer to the Ba sites.

3.2 Optical characteristics

For the justifications of variations and anomalies noticed in the optical spectra, it is normal routine to discuss transformations from occupied to unoccupied bands in the electronic energy band diagram particularly at those points depicting high symmetry in the Brillouin zone.^[38] On the basis of electronic configuration, dielectric function given by $\epsilon(\omega) = \epsilon_1(\omega) + i\epsilon_2(\omega)$ of BaCu₂As₂ and α-BaCu₂Sb₂ compounds was calculated. As these compounds are crystallized in the tetragonal symmetry {having space group D_{4h}^{17} I4/mmm for BaCu₂As₂ and D_{4h}^7 P4/nmm for α-

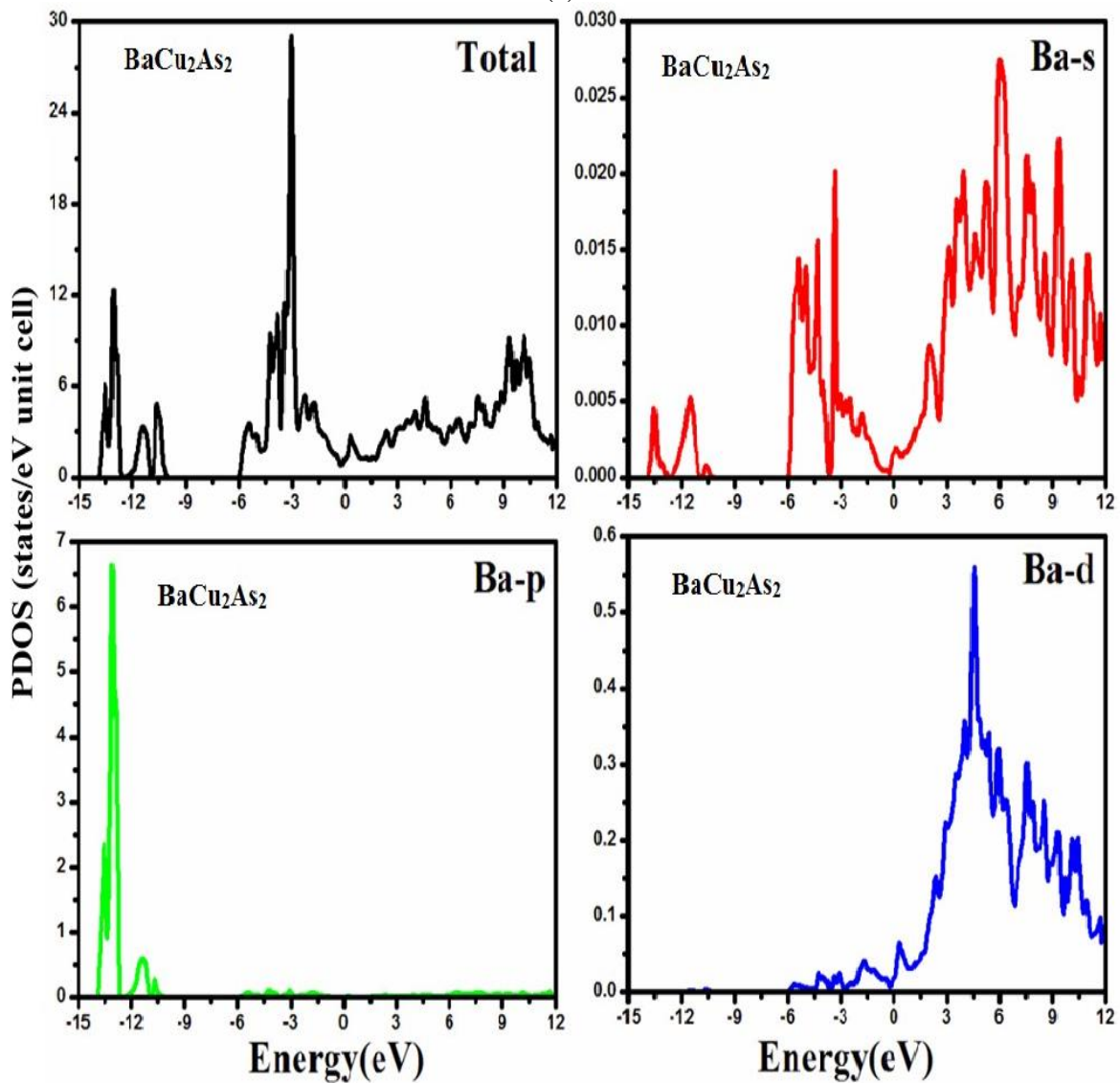
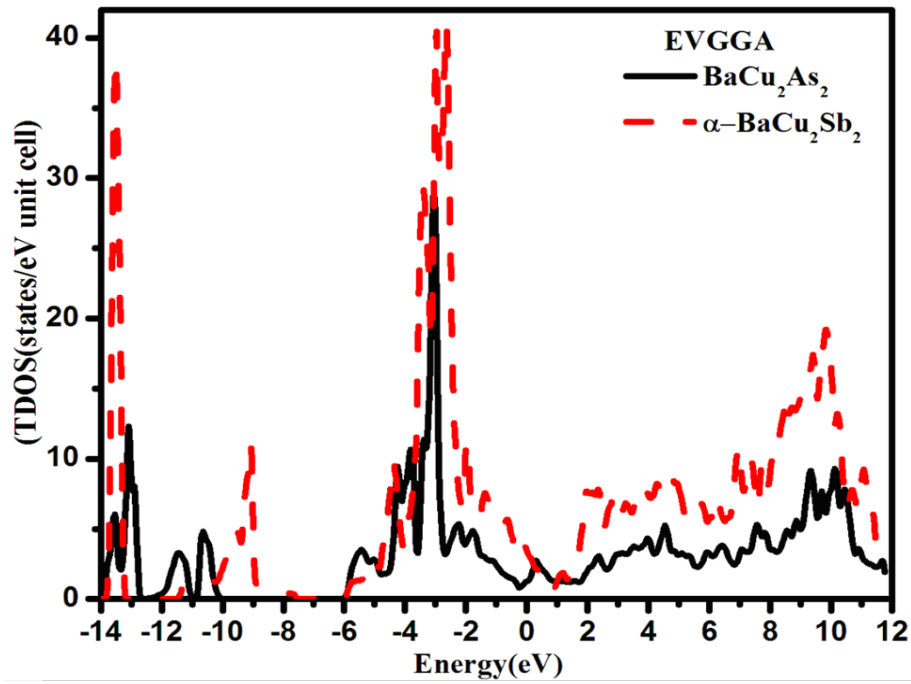
BaCu₂Sb₂^[22]. Such symmetry groups depend upon two dominantly independent components of dielectric tensor such as $\epsilon^{xx}(\omega) = \epsilon^{yy}(\omega)$ and $\epsilon^{zz}(\omega)$ associated with the applied electric field resulting from the polarization of light and are found perpendicular as well as parallel to the c-axis. As these two compounds show metallic nature that is why the intraband transitions related to Drude term hasve also been included in the calculations. Hence, the calculations involve the contributions of both the interband and the intraband transitions:

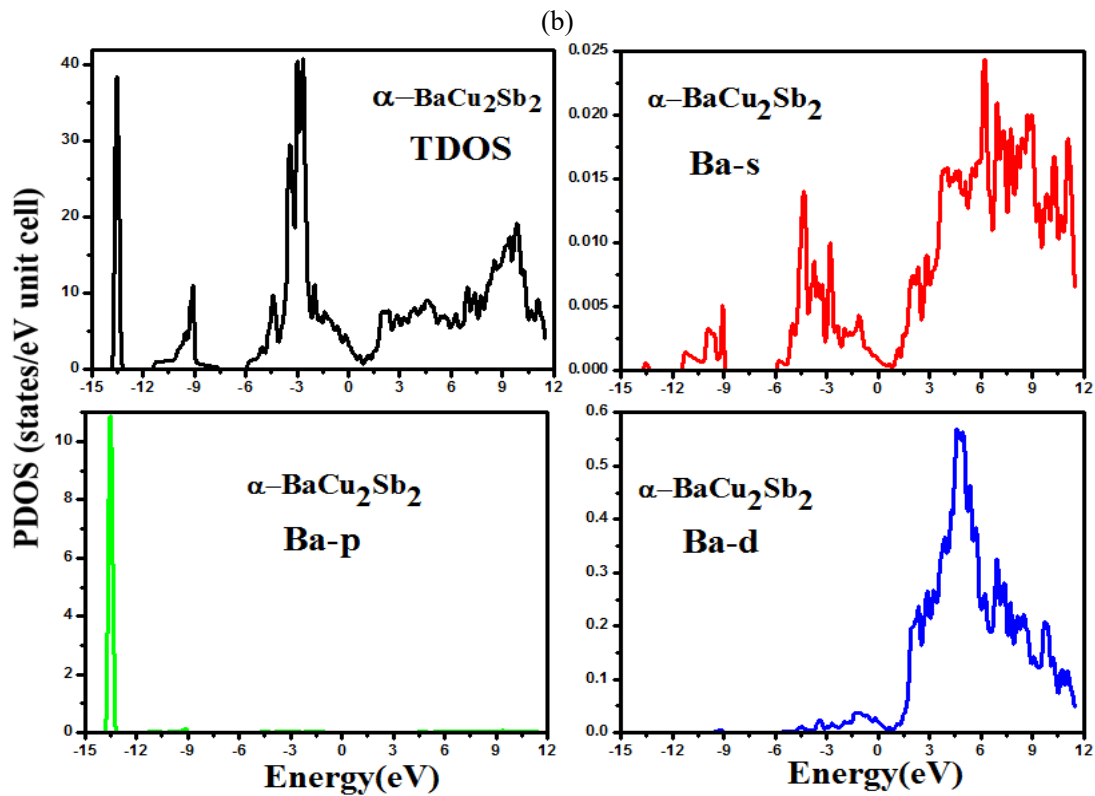
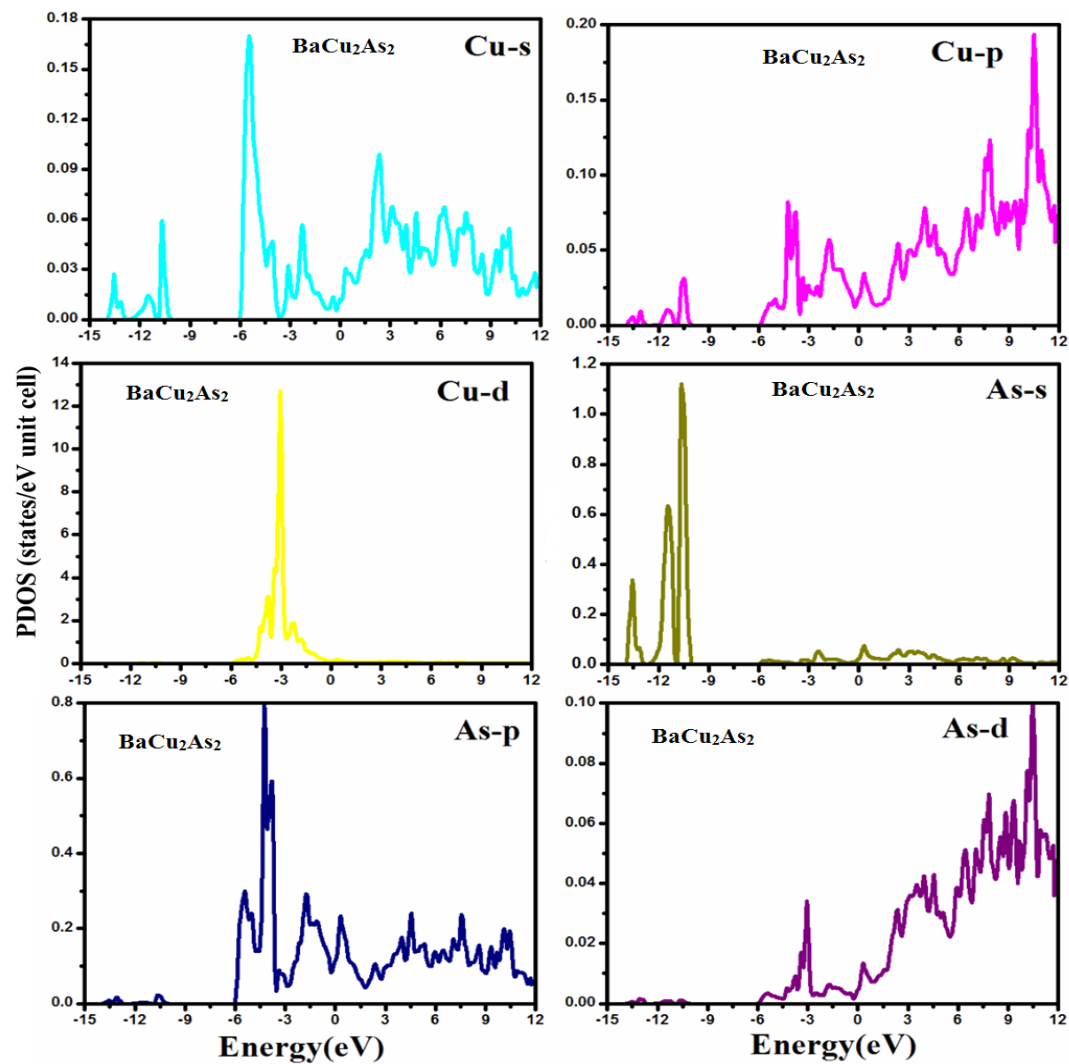
$$\epsilon_2(\omega) = \epsilon_{2,int er}(\omega) + \epsilon_{2,int ra}(\omega) \quad (3)$$

The calculated values of both the imaginary $\epsilon_2(\omega)$ and real $\epsilon_1(\omega)$ parts of dielectric function in terms of photon energy are presented in Figs. 4(a) and 4(b) respectively. Imaginary part $\epsilon_2(\omega)$ of the dielectric function has direct relation with the energy band structure.^[39] The VBM and the CBM are composed of Ba-*p*, As-*p* and Ba-*d* states respectively. The peaks are located between 0.0 to 5.0 eV for BaCu₂As₂ and between 0.0 to 6.0 eV for α-BaCu₂Sb₂ compounds corresponding to the transition from As/Sb-*p* VBM to Ba-*d* CBM. The peaks for the calculated components, $\epsilon_2^{xx}(\omega)$ and $\epsilon_2^{zz}(\omega)$, for BaCu₂As₂ compound lie at different energies however, for α-BaCu₂Sb₂ compound, these are located at almost same energy. Such variations of the imaginary component of dielectric function might be related with their slightly different symmetries. In addition, it is noteworthy that all the peaks observed in $\epsilon_2(\omega)$ are not related with a single interband transformation because a lot of direct to indirect transformations might occur in the band structure with an energy corresponding to the same peaks.^[40]

The real part of dielectric function $\epsilon_1(\omega)$ can be obtained from $\epsilon_2(\omega)$ using Kramers-Kronig (KK) relation. For real part the calculated components, $\epsilon_1^{xx}(\omega)$ and $\epsilon_1^{zz}(\omega)$, show sharp rise below or above 1.0 eV forming maxima at 1.0 or 1.5 eV for BaCu₂As₂ and at 2.0 or 2.3 eV for α-BaCu₂Sb₂ compounds as demonstrated in Fig. 4. Such a sharp rise might be caused by Drude term representing intraband transitions. There appears a substantial anisotropy noticed between $\epsilon_1^{xx}(\omega)$ and $\epsilon_1^{zz}(\omega)$ up to about 7.0 eV, but beyond this energy both components contribute almost equally.

Figure 5 displays the optical functions of BaCu₂As₂ and α-BaCu₂Sb₂ calculated in the photon energy range of up to 14.0 eV. Figs. 5(a) and 5(b) depict the calculated absorption spectra along xx and zz directions for the BaCu₂As₂ and α-BaCu₂Sb₂, respectively. These figures reveal that there exists an absorption band in the low energy range below 2.0 eV which might be caused by metallic nature of these compounds. This band shows strong character for the α-BaCu₂Sb₂ as compared to that of BaCu₂As₂. Moreover, strong anisotropy is noticeable in the absorption spectra of BaCu₂As₂ whereas α-BaCu₂Sb₂ depicts almost isotropic behavior. As evident from the band structures of these compounds (see Fig. 3) these materials show no band gap, therefore, photoconductivity initiates in both compounds when photon energy is zero, and hence there is a rise in photoconductivity (and consequently the electrical





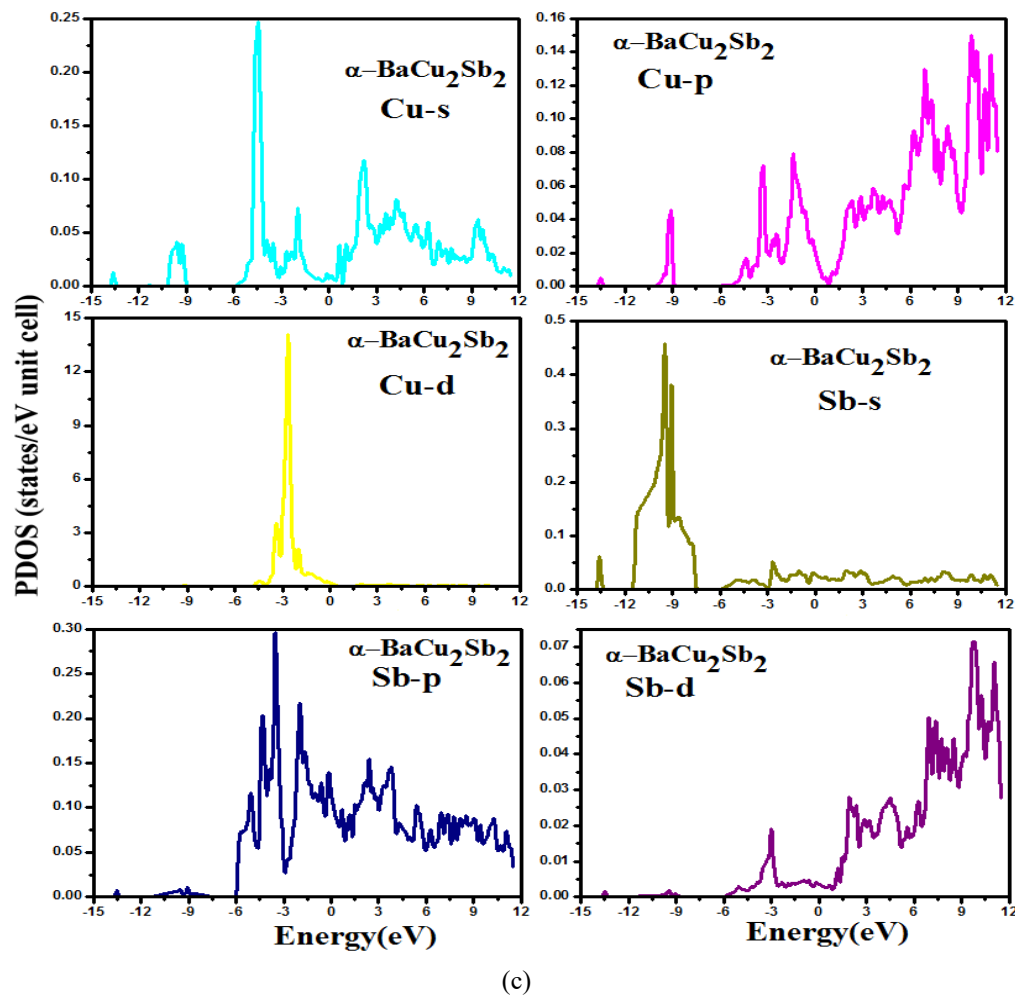


Fig. 3 Calculated total (a) and partial densities of states (States/eV unit cell) for BaCu₂As₂ (b) and for α -BaCu₂Sb₂ (c) compounds.

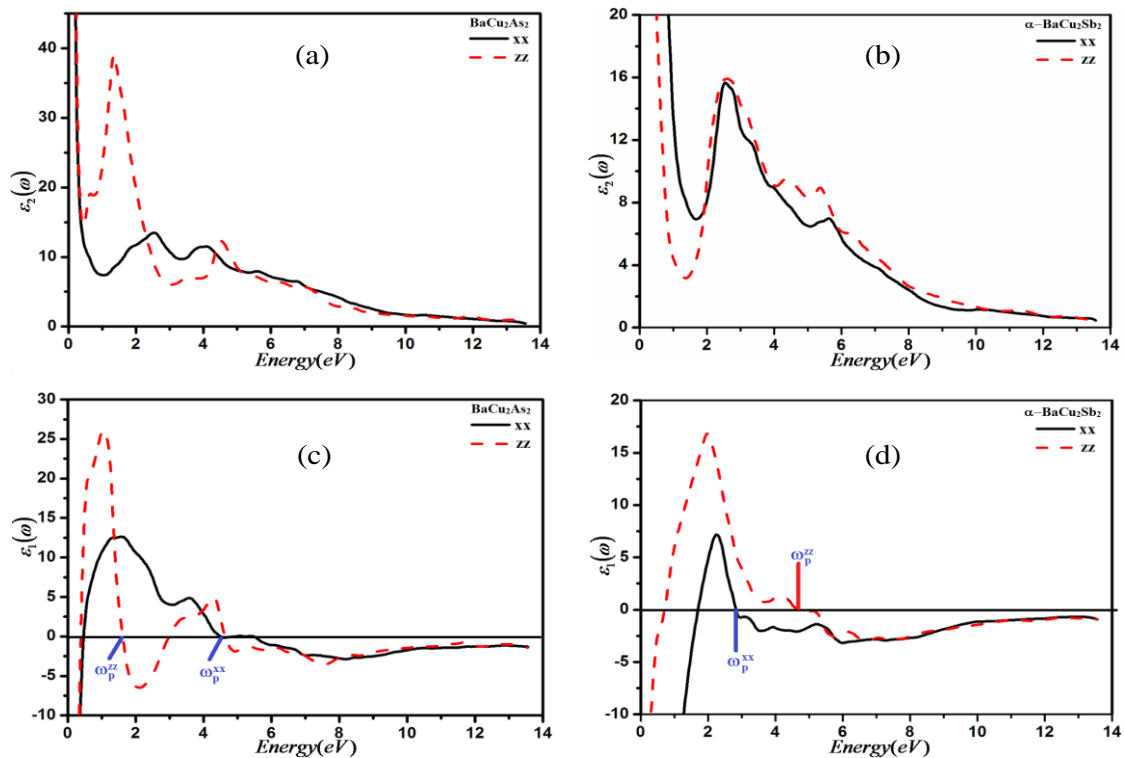


Fig. 4 Calculated imaginary $\epsilon_2(\omega)$ and real part $\epsilon_1(\omega)$ of dielectric function for BaCu₂As₂ (a, c) and for α -BaCu₂Sb₂ (b, d) compounds.

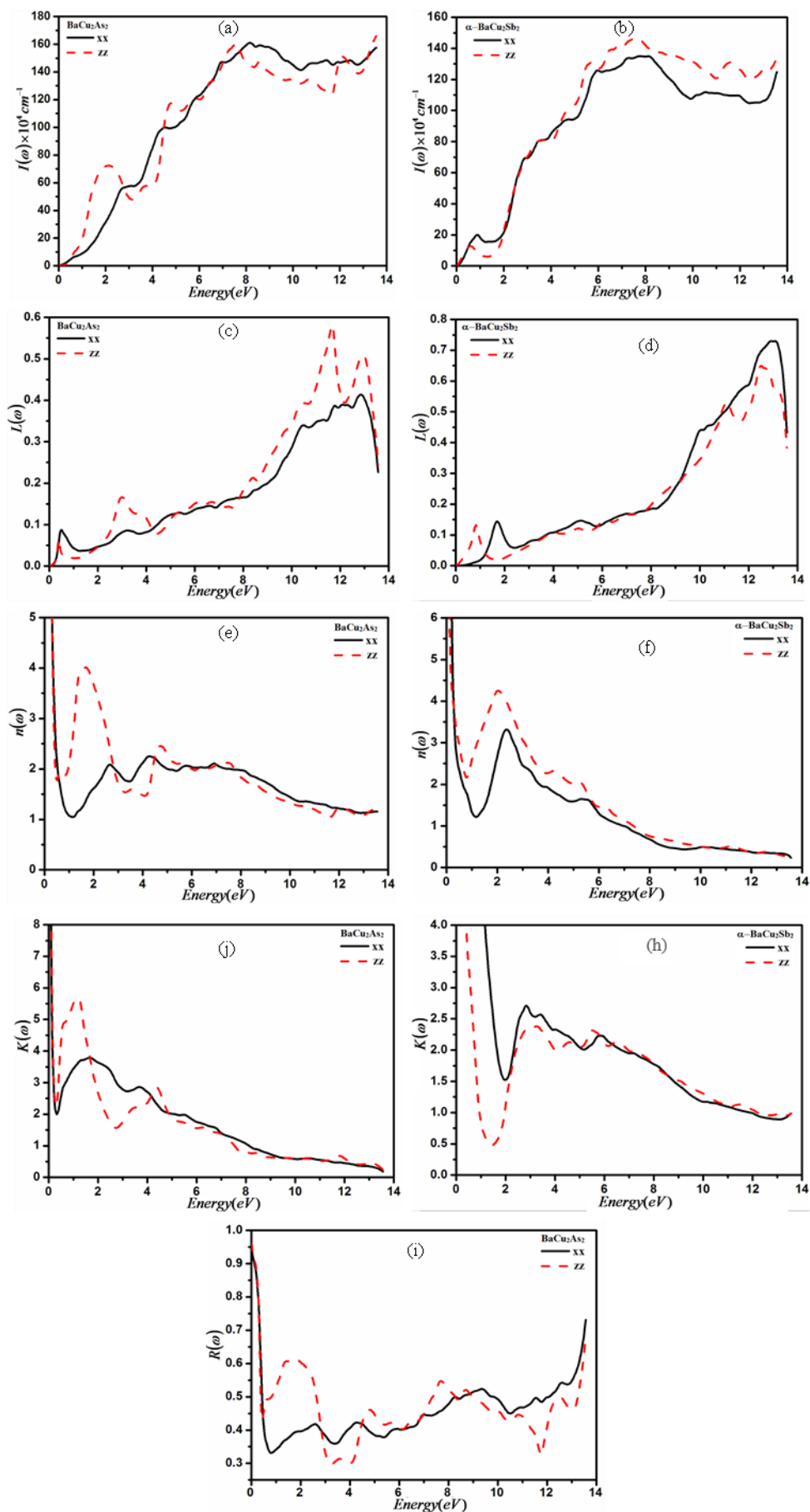


Fig. 5 (a,b) Calculated absorption spectra, (c, d) energy-loss spectra $L(\omega)$, (e, f) refractive index $n(\omega)$, (g, h) extinction co-efficient and (i, j) reflectivity $R(\omega)$ of $BaCu_2As_2$ and $\alpha-BaCu_2Sb_2$ compounds.

conductivity) of these materials by the absorption of photons.

The absorption spectrum of BaCu₂As₂ compound raises sharply at a faster rate than that of α -BaCu₂Sb₂ compound and illustrates some prominent peaks between 6.0 to 10.0 eV. The first two peaks might be attributed to the transitions from As-*p* to Ba-*d* states. Almost the same features can be seen in the investigated compounds.

The energy-loss spectrum $L(\omega)$ expresses the loss of energy by a fast moving electron traversing in a material.^[41] The most intense peak observed in $L(\omega)$ describes the frequency (energy) of combined vibrations of valence electrons inside a crystal and is known as the bulk plasma frequency ω_p , which arises when ϵ_1 approaches the zero value.^[27,42,43] Below ω_p materials illustrate the metallic characteristics (*i.e.* $\epsilon_1(\omega) < 0$).^[44] The energy-loss spectrum plot {Figs. 5(c, d)} reveals that the plasma frequencies ω_p are 3.20, 12.85 eV, and 2.94, 11.70 eV of $\omega_p^{xx}(\omega)$ and $\omega_p^{zz}(\omega)$, respectively for BaCu₂As₂ while their values for α -BaCu₂Sb₂ compounds are 5.10, 12.90 eV, and 5.00, 12.50 eV, respectively as obvious from Figs. 5(c, d). Therefore, as the energy of incident light goes beyond 12.85 eV along xx direction and 11.70 eV along zz orientation, BaCu₂As₂ compound becomes transparent. Similarly, for α -BaCu₂Sb₂ compound, on raising the frequency of incident light higher than 12.90 eV along xx component and 12.50 eV along zz component, the compound depicts transparent trend. The peaks observed around 12.0 eV are plasma resonances related to the frequency of combined vibrations of valence electrons. However, other peaks might be attributed to excitons and other interband transformations.^[27] Since the high-flying climax for $L^{xx}(\omega) = L^{yy}(\omega)$ and $L^{zz}(\omega)$ spectra symbolizes the feature connected with the plasma resonance.^[44,45]

The refractive index {having components $n^{xx}(\omega)$ and $n^{zz}(\omega)$ } and the extinction coefficient {with components $K^{xx}(\omega)$ and $K^{zz}(\omega)$ } related to the complex refractive index have been presented in Figs. 5(e-h). The refractive index $n(\omega)$ also reveals strong anisotropy for the BaCu₂As₂ compound however; its trend for α -BaCu₂Sb₂ compound is almost identical. For both compounds, the real part, *n* and the imaginary part, *k* of refractive index demonstrate decreasing trend at high energies as obvious from Figs. 5(e - h).

The calculated reflectivity of BaCu₂As₂ and α -BaCu₂Sb₂ as a function of photon energy is presented in Figs. 5(i, j). A sudden fall of reflectivity at low energies for both compounds may be associated with their high conductance.^[39] It is further noticed that the magnitude of reflectivity for α -BaCu₂Sb₂ is somewhat higher than that of BaCu₂As₂, which means that the ability of reflecting solar light in α -BaCu₂Sb₂ compound is more robust than that of BaCu₂As₂.

4. Conclusions

The electronic structure and optical properties have been predicted for the BaCu₂As₂ and α -BaCu₂Sb₂ compounds. The electronic band structures show the metallic behavior of both compounds. It is observed from the density of states plot that

the whole curve of α -BaCu₂Sb₂ is shifted towards higher energies about 0.1 eV with respect to BaCu₂As₂; and also the peaks of the TDOS for BaCu₂As₂ compound are smaller than that of α -BaCu₂Sb₂ compound. The band structure helps to discuss the origin of the features that appear in the optical properties. The reflectivity spectrum shows that the predicted compound BaCu₂As₂ is a better candidate as compared to those of α -BaCu₂Sb₂ compounds as a coating material to avoid solar heating than the improved behavior in reflectivity.

Conflict of Interest

There is no conflict of interest.

Supporting Information

Not applicable.

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